N-Channel Enhancement Mode MOSFET

BL008N04TH-TL

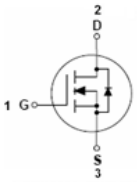
Features

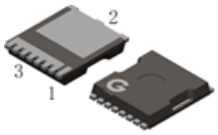
- Advanced Shielded-Gate Trench technology
- Ultra-low on-resistance
- Superior thermal resistance
- HBM: JESD22-A114-B: 2
- RoHS compliant with Halogen-free

HF

Mechanical Data

- Case: TOLL
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208





TOLL

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BL008N04TH-TL	TOLL	2000 pcs / Tape & Reel	008N04TH

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	40	V
Gate-to-Source Voltage	V_{GSS}	±20	V
Continuous Drain Current (Package limited)	I_D	350	A
Continuous Drain Current (T_C = 25°C, Silicon Limited)		500	
Continuous Drain Current (T_C = 100°C)		350	
Continuous Drain Current (T_A = 25°C) *1		50	
Continuous Drain Current (T_A = 100°C) *1		35	
Pulsed Drain Current (t_p = 10μs, T_C = 25°C)	I_{DM}	2000	A
Single Pulse Avalanche Energy *3	E_{AS}	1400	mJ
Power Dissipation (T_C = 25°C)	P_D	375	W
Operating Junction Temperature Range	T_J	-55 ~ +175	°C
Storage Temperature Range	T_{STG}	-55 ~ +175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	0.34	0.4	°C/W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	35	40	°C/W

Electrical Characteristics (@ T_J = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	40	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 40V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *2	V_{GS} = 10V,I_D = 100A	-	0.6	0.8	mΩ
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2	2.9	4	V
R_G	Gate Resistance	V_{GS} = 0V, f = 1MHz	-	1.2	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V V_{DS} = 25V f = 100kHz	-	12860	-	pF
C_{OSS}	Output Capacitance		-	2565	-	
C_{RSS}	Reverse Transfer Capacitance		-	130	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time	V_{DD} = 30V V_{GS} = 15V I_D = 30A R_G = 3.3Ω	-	52	-	ns
t_r	Turn-on Rise Time		-	143	-	
$t_{d(OFF)}$	Turn-Off Delay Time		-	130	-	
t_f	Turn-Off Fall Time		-	17	-	
Q_G	Total Gate-Charge	V_{DD} = 32V V_{GS} = 10V I_D = 100A	-	165	-	nC
Q_{GS}	Gate to Source Charge		-	56	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	27	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *2	I_S = 100A, V_{GS} = 0V	-	0.8	1.2	V
trr	Reverse Recovery Time	I_F = 40A, V_{GS} = 0V di/dt = 100A/μs	-	112	-	ns
Qrr	Reverse Recovery Charge		-	265	-	nC

Notes:

1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating. The test condition is V_{DD} = 30V, V_{GS} = 10V, L = 0.5mH

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

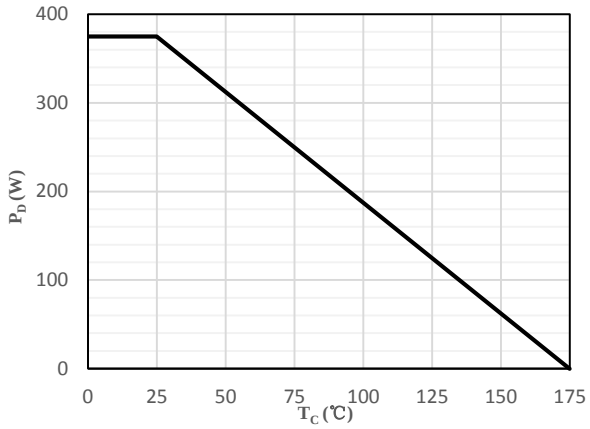


Fig 1 Power Dissipation

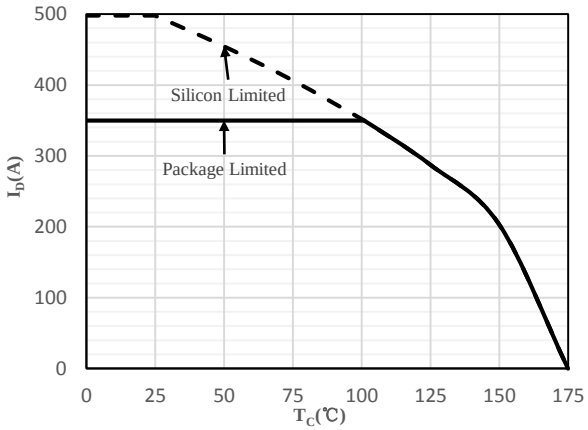


Fig 2 Drain Current

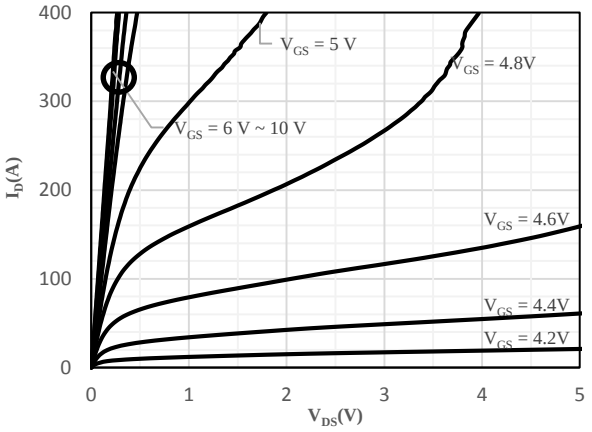


Fig 3 Typical Output Characteristics

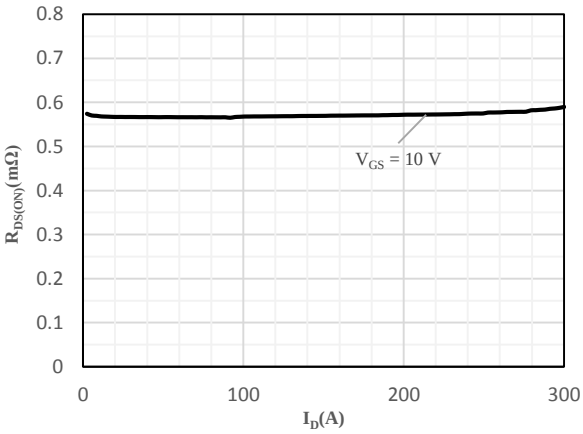


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

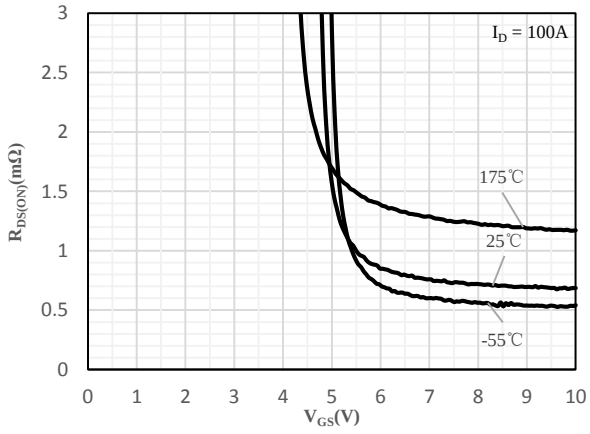


Fig 5 On-Resistance vs. Gate-Source Voltage

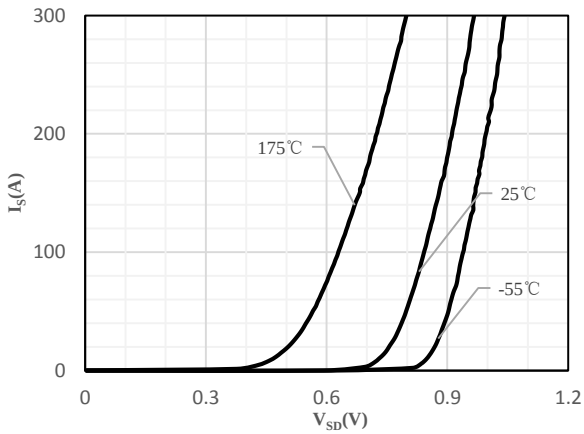


Fig 6 Body-Diode Characteristics

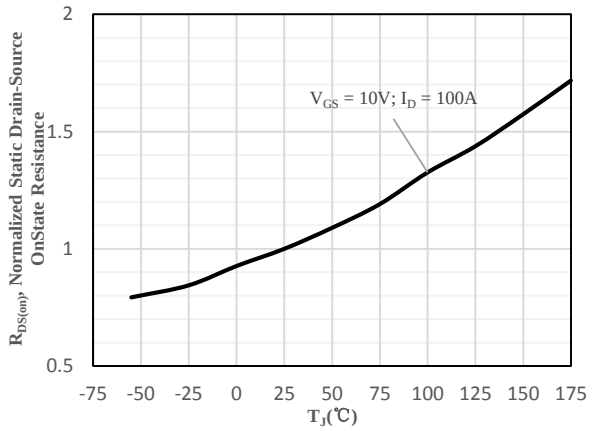


Fig 7 Normalized On-Resistance vs. Junction Temperature

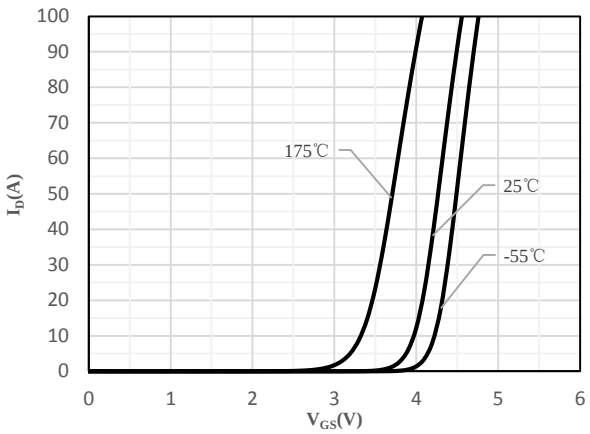


Fig 8 Transfer Characteristics

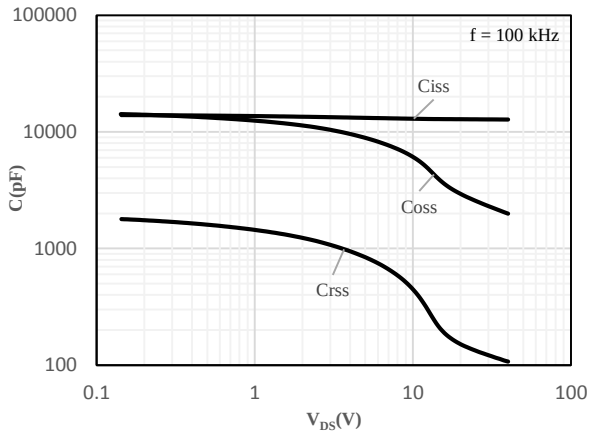


Fig 9 Capacitance Characteristics

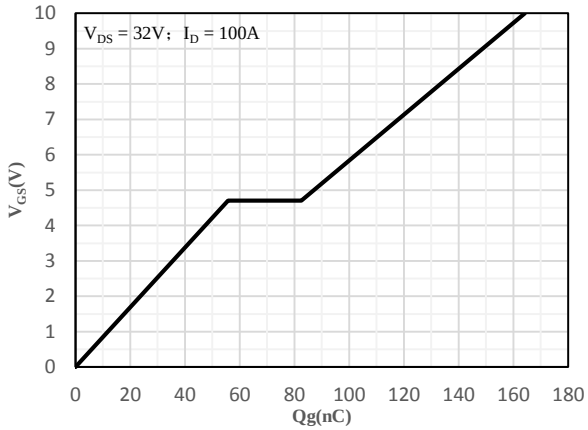


Fig 10 Gate-Charge Characteristics

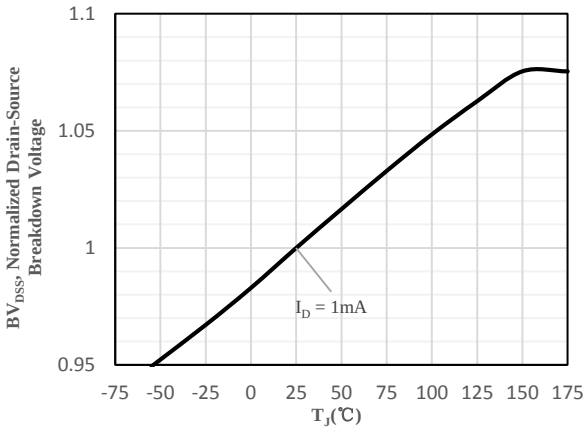


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

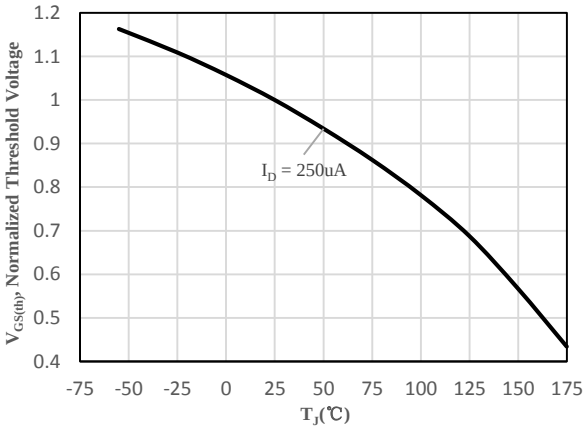


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

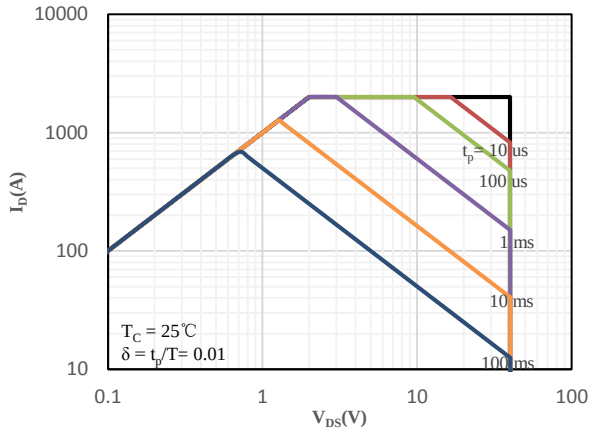


Fig 13 Safe Operating Area

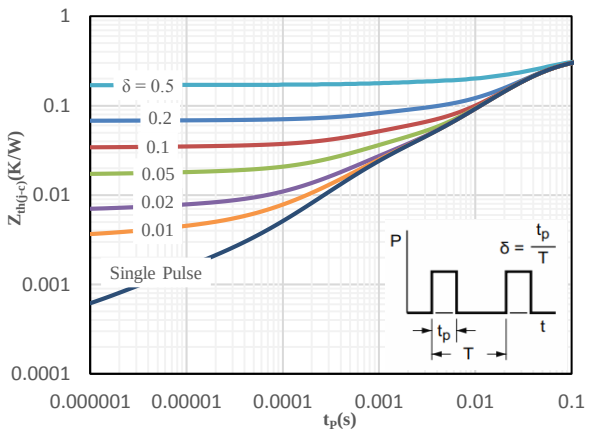
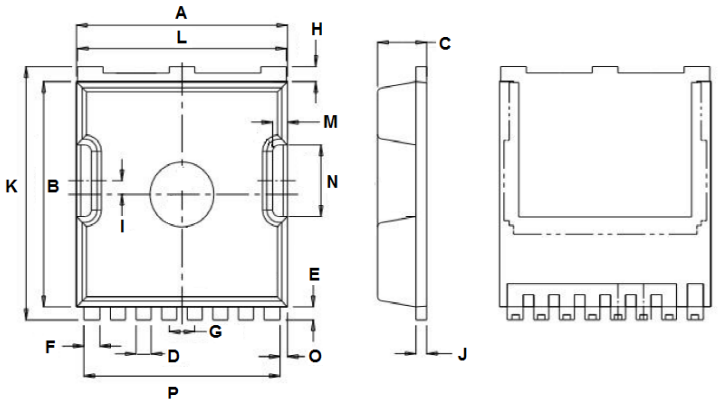


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



TOLL		
Dimension	**Min.**	**Max.**
A	9.70	10.10
B	10.20	10.60
C	2.10	2.50
D	0.60	0.80
E	0.50	0.70
F	0.65	0.85
G	1.10	1.30
H	0.60	0.80
I	0.55	0.75
J	0.45	0.55
K	11.50	11.90
L	9.60	10.00
M	0.50	0.70
N	3.10	3.50
O	0.25	0.45
P	9.00	9.40

SOLDERING FOOTPRINT (Unit: mm)